



SHEET OF

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 205109US20DIV		SERIAL NO. 09/822,335	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Paul M. ENQUIST			
				FILING DATE RCE Filed July 24, 2003		GROUP 2814	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>W</i>	AA	5,841,197	11/1998	Adamic, Jr.	<i>11</i>	<i>11</i>	
<i>W</i>	AB	5,185,274	02/1993	Chang et al.	<i>11</i>	<i>11</i>	
<i>W</i>	AC	5,296,390	03/1994	Awano	<i>11</i>	<i>11</i>	
<i>W</i>	AD	5,504,359	04/1996	Rodder	<i>11</i>	<i>11</i>	
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
	AM						
	AN						
	AO						
	AP						
	AQ						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
<i>W</i>	AR	Submicron Lateral Scaling of Vertical-Transport Devices: Transferred-Substrate Bipolar Transistors and Schottky-Collector Tunnel Diodes; M. Rodwell et al.; Invited Paper, 1997 OSA Ultrafast Electronics and Optoelectronics Conference					
<i>W</i>	AS	A 277-GHz $F_{max}$ Transferred-Substrate Heterojunction Bipolar Transistor; B. Agarwal et al.; IEEE Electron Device Letters, Vol. 18, No. 5, May 1997, pgs. 228-231					
<i>W</i>	AT	Transferred Substrate Schottky-Collector Heterojunction Bipolar Transistors: First Results and Scaling Laws for High $F_{max}$ ; U. Bhattacharya, et al.; IEEE Electron Device Letters, Vol. 16, No. 8, August 1995, pgs. 357, 359					
<i>W</i>	AU	A > 400 Ghz $F_{max}$ Transferred-Substrate HBT Integrated Circuit Technology; R. Pallela et al.; DRC 1997					
<i>W</i>	AV	Deep Submicron Transferred-Substrate Heterojunction Bipolar Transistors; Q. Lee et al.; DRC 1998					
<i>W</i>	AW	170 GHz Transferred-Substrate Heterojunction Bipolar Transistor; U. Bhattacharya et al.; Electronics Letters, 18 <sup>th</sup> July 1996, vol. 32, No. 15, pgs. 1405-6					
<i>W</i>	AX	Transferred Substrate Heterojunction Bipolar Transistors; Dissertation by U. Bhattacharya, Nov. 27, 1996					
<i>W</i>	AY	Digital Integrated Circuits in the Transferred-Substrate HBT Technology, Dissertation by R. Pallela, June 1998					
	AZ					<input type="checkbox"/> Additional References sheet(s) attached	
Examiner <i>Mjm</i> <i>W</i> <i>Mj</i>					Date Considered <i>7-8-04</i>		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							